FAIRCHILD SEMICONDUCTOR®

July 2007

FDP100N10

N-Channel PowerTrench® MOSFET

100V, 75A, 10mΩ

Features

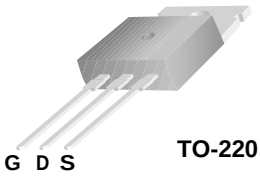
- $R_{DS(on)}$ = 8.2mΩ (Typ.)@ V_{GS} = 10V, I_D = 75A
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low $R_{DS(on)}$
- High power and current handing capability
- RoHS compliant

Applications

- DC to DC converters / Synchronous Rectification

Description

This N-Channel MOSFET is producedusing Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.



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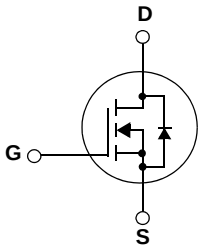


MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current	-Continuous (T_C = 75°C)	75	A
I_{DM}	Drain Current	- Pulsed (Note 1)	300	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	365	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.8	V/ns
P_D	Power Dissipation	(T_C = 25°C)	208	W
		- Derate above 25°C	1.4	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.72	°C/W
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

*When mounted on the minimum pad size recommended (PCB Mount)

Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP100N10	FDP100N10	TO-220	-	-	50

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V, $T_J = 25^oC$	100	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25^oC	-	0.1	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 100V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 100V, V_{GS} = 0V, $T_J = 150^oC$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 75A	-	8.2	10	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 37.5A (Note 4)	-	110	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	5500	7300	pF
C_{oss}	Output Capacitance		-	530	710	pF
C_{rss}	Reverse Transfer Capacitance		-	220	325	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 50V, I_D = 75A, V_{GS} = 10V (Note 4, 5)	-	76	100	nC
Q_{gs}	Gate to Source Gate Charge		-	30	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	20	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V, I_D = 75A, V_{GS} = 10V, R_{GEN} = 25Ω (Note 4, 5)	-	70	150	ns
t_r	Turn-On Rise Time		-	265	540	ns
$t_{d(off)}$	Turn-Off Delay Time		-	125	260	ns
t_f	Turn-Off Fall Time		-	115	240	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	75	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 75A	-	-	1.25	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 75A, dI_F/dt = 100A/μs (Note 4)	-	71	-	ns
Q_{rr}	Reverse Recovery Charge		-	164	-	nC

Notes:
1: Repetitive Rating: Pulse width limited by maximum junction temperature
2: L = 0.13mH, I_{AS} = 75A, V_{DD} = 25V, R_G = 25Ω, Starting $T_J = 25^oC$
3: I_{SD} ≤ 75A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting $T_J = 25^oC$
4: Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

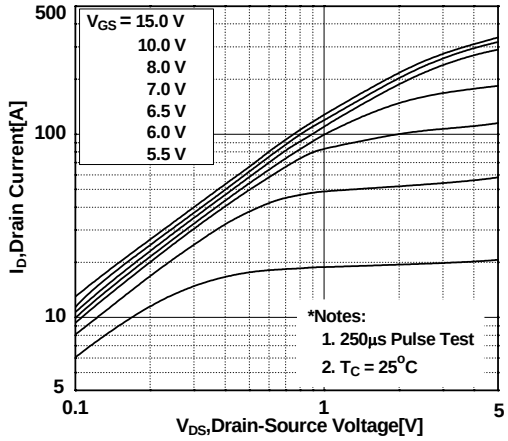


Figure 2. Transfer Characteristics

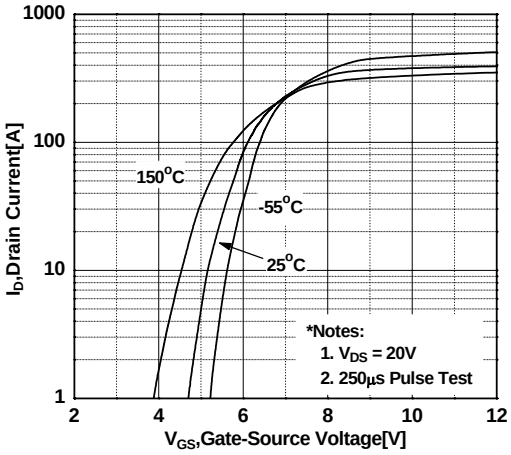


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

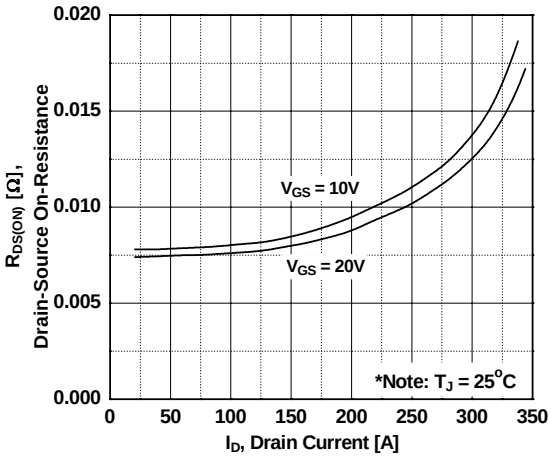


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

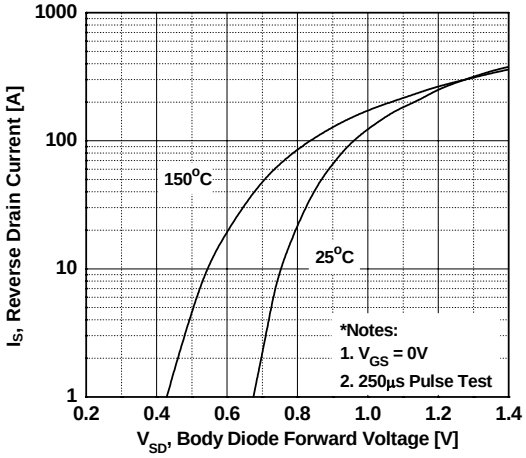


Figure 5. Capacitance Characteristics

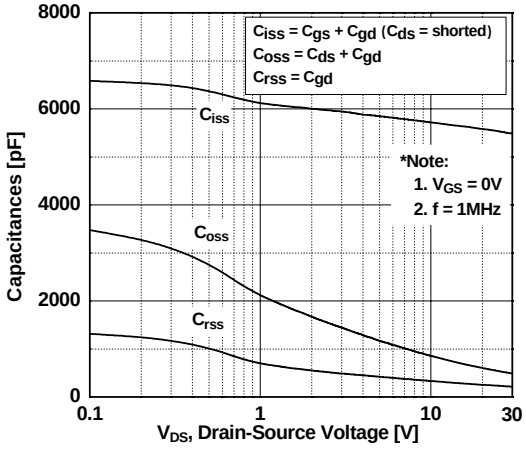
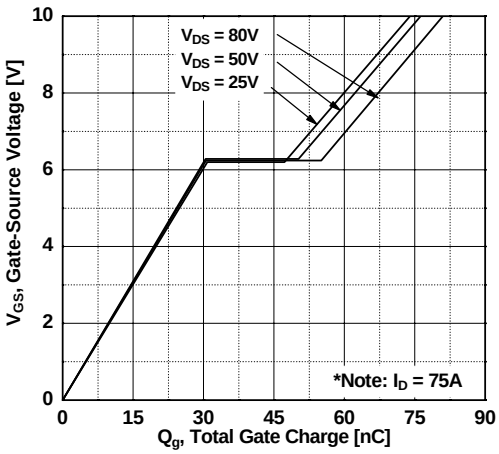


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

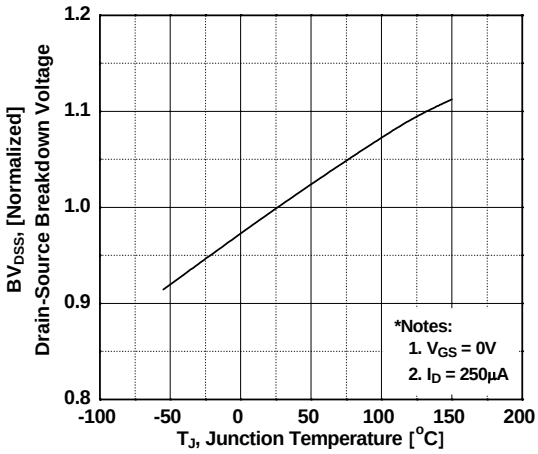


Figure 8. On-Resistance Variation vs. Temperature

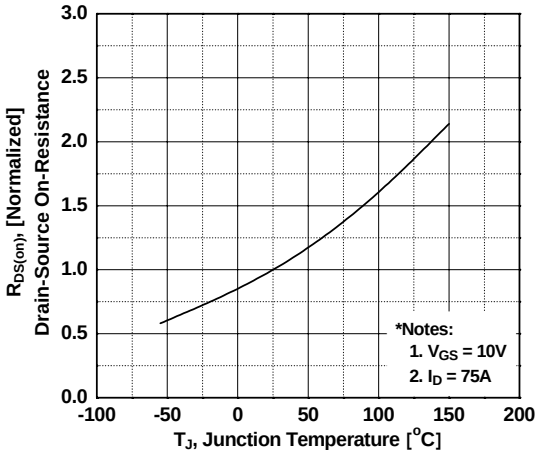


Figure 9. Maximum Safe Operating Area

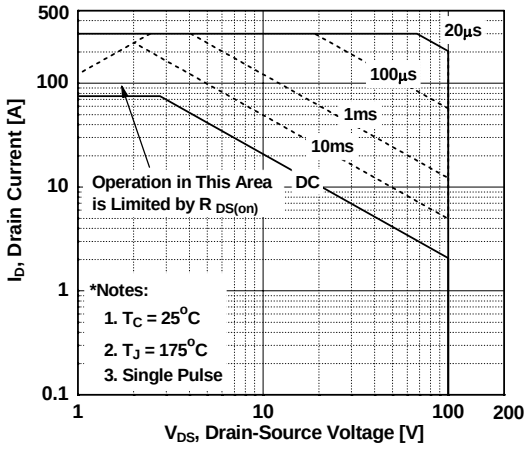


Figure 10. Maximum Drain Current vs. Case Temperature

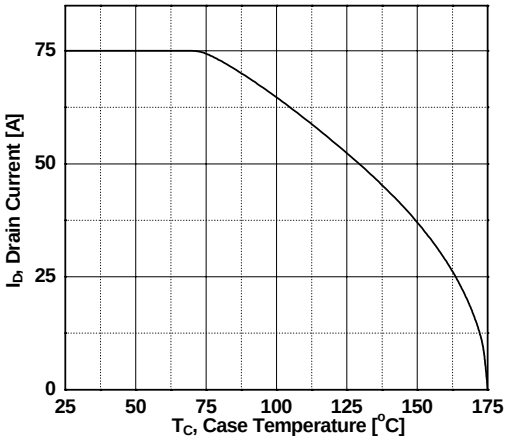
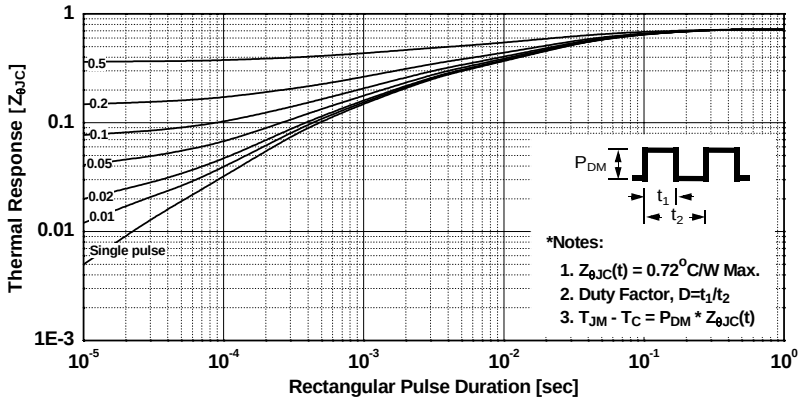
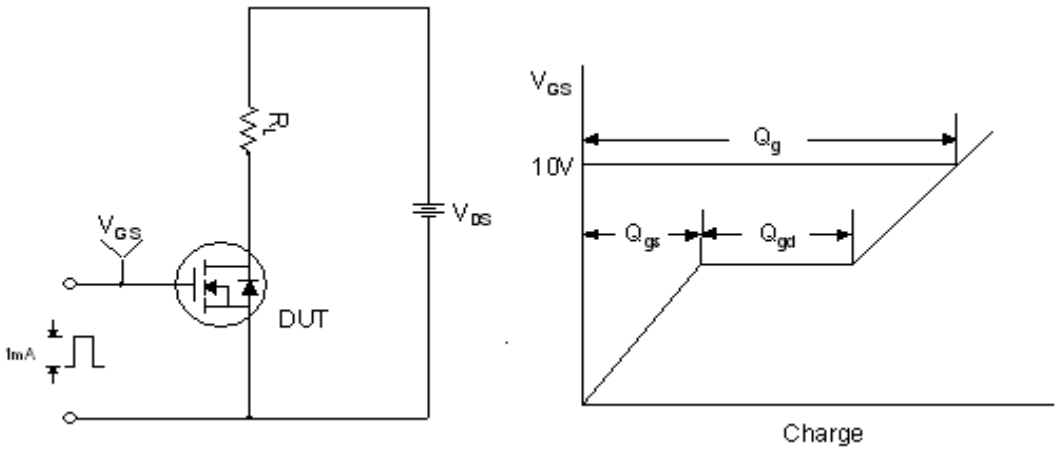


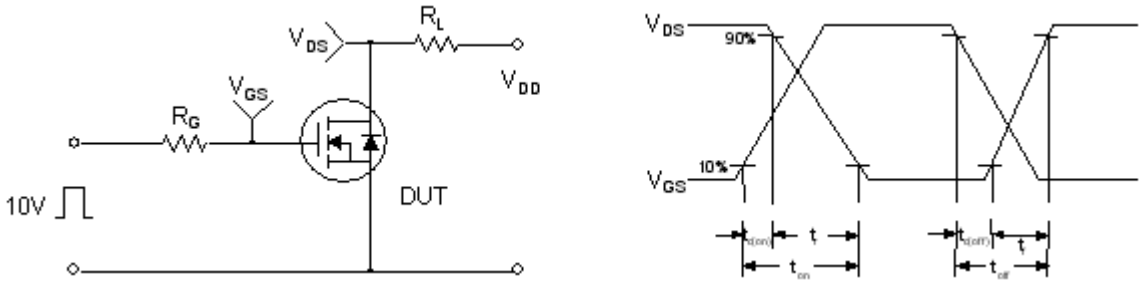
Figure 11. Transient Thermal Response Curve



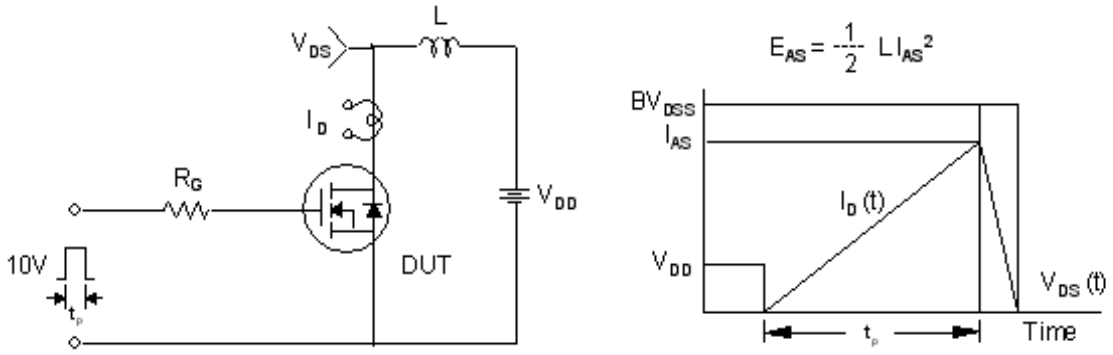
Gate Charge Test Circuit & Waveform



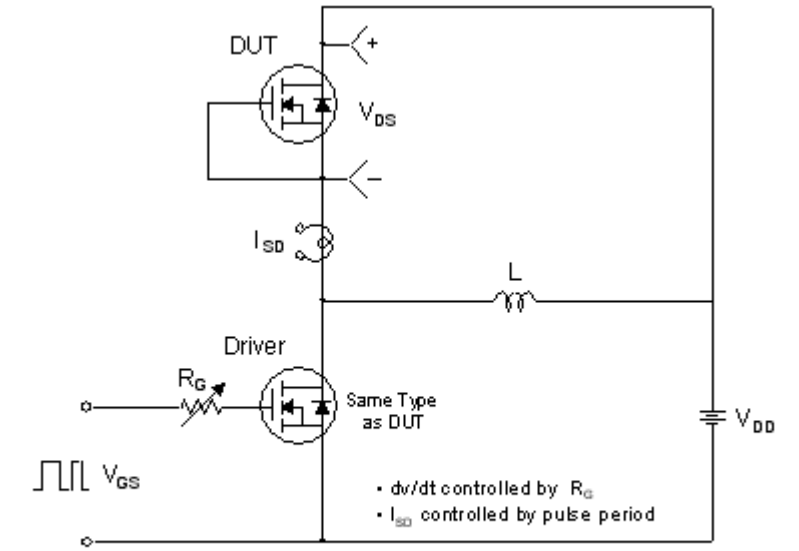
Resistive Switching Test Circuit & Waveforms

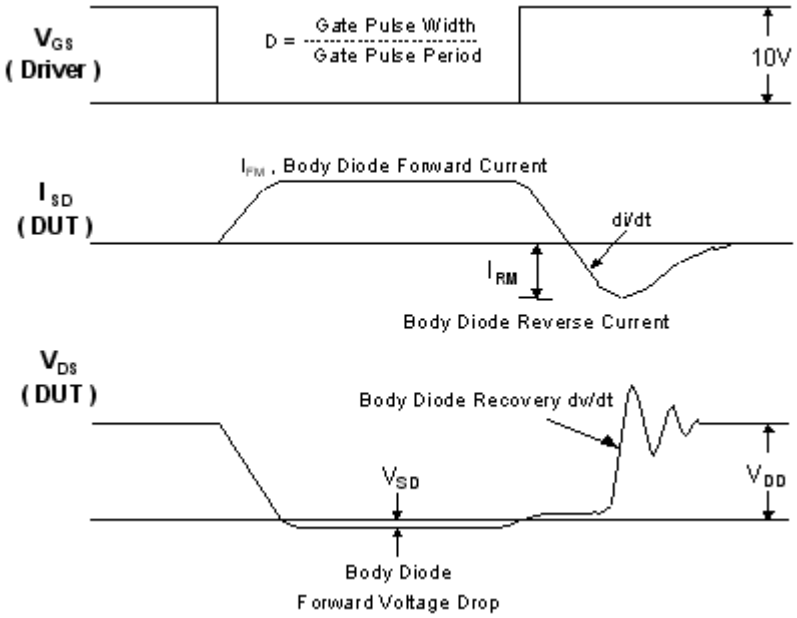


Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

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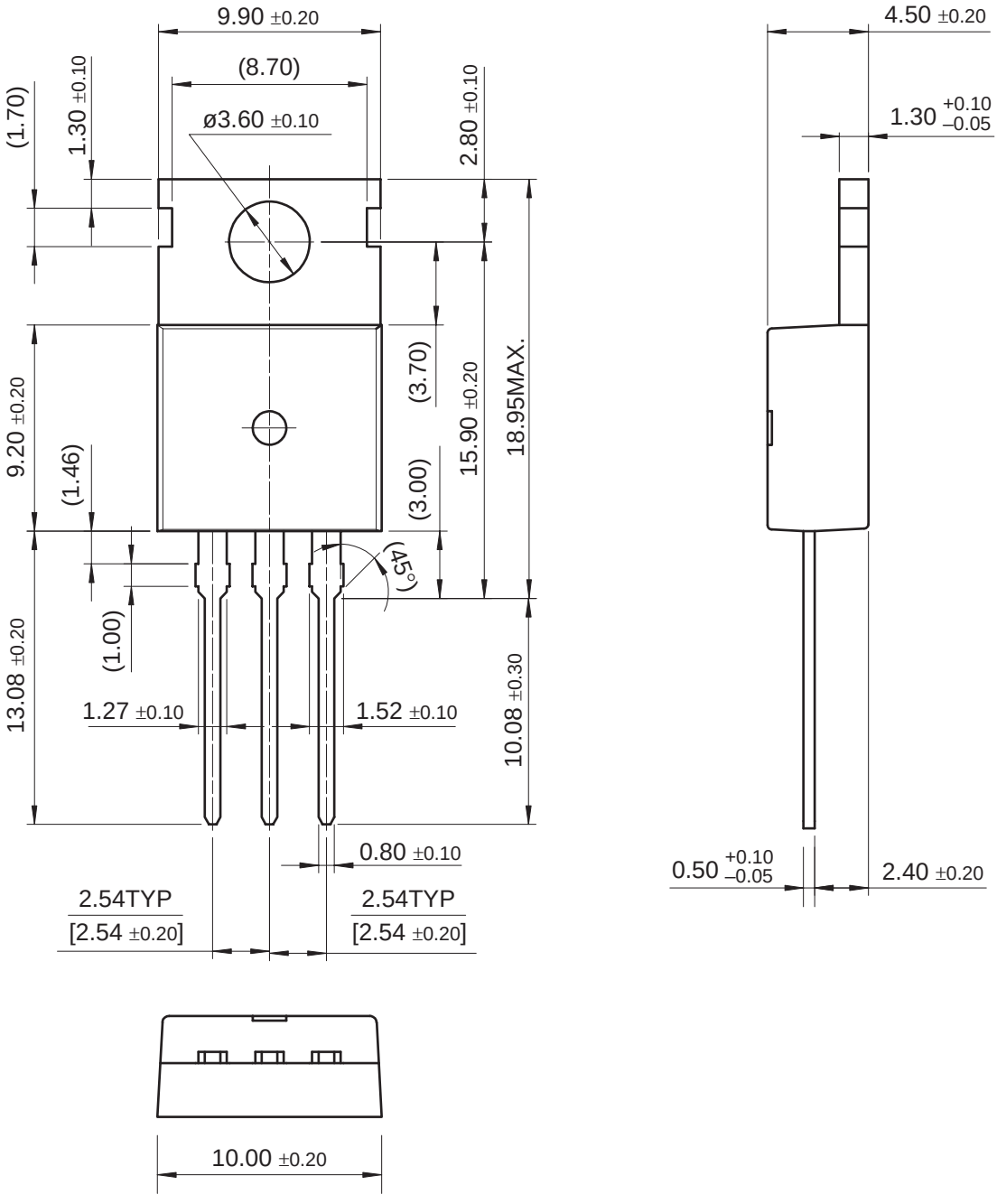

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